74AUP1G38

Low-power 2-input NAND gate (open drain) Rev. 6 — 28 June 2012

Product data sheet

General description 1.

The 74AUP1G38 provides the single 2-input NAND gate with open-drain output. The output of the device is an open drain and can be connected to other open-drain outputs to implement active-LOW wired-OR or active-HIGH wired-AND functions.

Schmitt trigger action at all inputs makes the circuit tolerant to slower input rise and fall times across the entire V_{CC} range from 0.8 V to 3.6 V.

This device ensures a very low static and dynamic power consumption across the entire V_{CC} range from 0.8 V to 3.6 V.

This device is fully specified for partial power-down applications using I_{OFF}. The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

2. **Features and benefits**

- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- Complies with JEDEC standards:
 - ◆ JESD8-12 (0.8 V to 1.3 V)
 - ◆ JESD8-11 (0.9 V to 1.65 V)
 - ◆ JESD8-7 (1.2 V to 1.95 V)
 - ◆ JESD8-5 (1.8 V to 2.7 V)
 - ◆ JESD8-B (2.7 V to 3.6 V)
- ESD protection:
 - HBM JESD22-A114F Class 3A exceeds 5000 V
 - MM JESD22-A115-A exceeds 200 V
 - CDM JESD22-C101E exceeds 1000 V
- Low static power consumption; $I_{CC} = 0.9 \mu A$ (maximum)
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V_{CC}
- I_{OFF} circuitry provides partial power-down mode operation
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C



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3. Ordering information

Table 1. Ordering information

Type number	Package									
	Temperature range	Name	Description	Version						
74AUP1G38GW	–40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1						
74AUP1G38GM	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 \times 1.45 \times 0.5 mm	SOT886						
74AUP1G38GF	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 \times 1 \times 0.5 mm	SOT891						
74AUP1G38GN	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $0.9 \times 1.0 \times 0.35$ mm	SOT1115						
74AUP1G38GS	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body 1.0 \times 1.0 \times 0.35 mm	SOT1202						
74AUP1G38GX	–40 °C to +125 °C	X2SON5	X2SON5: plastic thermal enhanced extremely thin small outline package; no leads; 5 terminals; body $0.8 \times 0.8 \times 0.35$ mm	SOT1226						

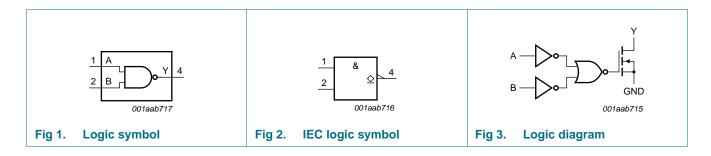
4. Marking

Table 2. Marking

Type number	Marking code ^[1]
74AUP1G38GW	аВ
74AUP1G38GM	аВ
74AUP1G38GF	аВ
74AUP1G38GN	аВ
74AUP1G38GS	аВ
74AUP1G38GX	аВ

^[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

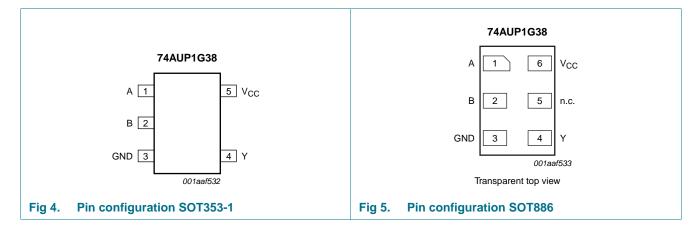
5. Functional diagram



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6. Pinning information

6.1 Pinning





6.2 Pin description

Table 3. Pin description

Symbol	Pin		Description
	TSSOP5 and X2SON5	XSON6	
Α	1	1	data input
В	2	2	data input
GND	3	3	ground (0 V)
Υ	4	4	data output
n.c.	-	5	not connected
V _{CC}	5	6	supply voltage

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7. Functional description

Table 4. Function table[1]

Input	Output	
Α	В	Υ
L	L	Z
L	Н	Z
Н	L	Z
Н	Н	L

^[1] H = HIGH voltage level;

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

		3 , ()		10	,
Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+4.6	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
VI	input voltage		[<u>1</u>] -0.5	+4.6	V
I _{OK}	output clamping current	V _O < 0 V	-50	-	mA
Vo	output voltage	Active mode and Power-down mode	[<u>1</u>] -0.5	+4.6	V
Io	output current	$V_O = 0 V \text{ to } V_{CC}$	-	+20	mA
I _{CC}	supply current		-	+50	mA
I _{GND}	ground current		-50	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}$	[2] _	250	mW

^[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		0.8	3.6	V
VI	input voltage		0	3.6	V
V _O	output voltage	Active mode and Power-down mode	0	3.6	V
T _{amb}	ambient temperature		-40	+125	°C
Δt/ΔV	input transition rise and fall rate	$V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	0	200	ns/V

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L = LOW voltage level;

Z = high-impedance OFF state.

^[2] For TSSOP5 packages: above 87.5 °C the value of P_{tot} derates linearly with 4.0 mW/K.
For XSON6 and X2SON5 packages: above 118 °C the value of P_{tot} derates linearly with 7.8 mW/K.

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10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = 2	5 °C					
V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	$0.70 \times V_{CC}$	-	-	V
		V _{CC} = 0.9 V to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 0.8 V	-	-	0.30 × V _{CC}	V
		V _{CC} = 0.9 V to 1.95 V	-	-	0.35 × V _{CC}	V
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	٧
V _{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = 20 \mu A$; $V_{CC} = 0.8 \text{ V}$ to 3.6 V	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	$0.3 \times V_{CC}$	V
		$I_O = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.31	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.31	V
		$I_O = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.31	٧
		$I_O = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.44	V
		$I_O = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.31	٧
		$I_O = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.44	٧
l _l	input leakage current	$V_I = GND$ to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.1	μΑ
l _{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL} (and at least one input LOW); $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.1	μА
I _{OFF}	power-off leakage current	V_I or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	±0.2	μΑ
ΔI_{OFF}	additional power-off leakage current	V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.2	μΑ
I _{CC}	supply current	V_I = GND or V_{CC} ; I_O = 0 A; V_{CC} = 0.8 V to 3.6 V	-	-	0.5	μΑ
Δl _{CC}	additional supply current	$V_I = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A}; V_{CC} = 3.3 \text{ V}$	-	-	40	μΑ
Cı	input capacitance	V_{CC} = 0 V to 3.6 V; V_I = GND or V_{CC}	-	8.0	-	pF
Co	output capacitance	output enabled; $V_O = GND$; $V_{CC} = 0 V$	-	1.7	-	pF
		output disabled; $V_O = GND$; $V_{CC} = 0 V$	-	1.1	-	pF
T _{amb} = -	40 °C to +85 °C					
V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	$0.70 \times V_{CC}$	-	-	V
		V _{CC} = 0.9 V to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0			V

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Table 7. Static characteristics ...continued
At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Uni
√ _{IL}	LOW-level input voltage	$V_{CC} = 0.8 V$	-	-	$0.30 \times V_{CC}$	V
		V _{CC} = 0.9 V to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V
/ _{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		I_O = 20 μ A; V_{CC} = 0.8 V to 3.6 V	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	$0.3 \times V_{CC}$	V
		$I_{O} = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.37	V
		$I_O = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.35	V
		$I_{O} = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.33	V
		$I_O = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.45	V
		$I_{O} = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.33	V
		$I_{O} = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.45	V
I	input leakage current	V_I = GND to 3.6 V; V_{CC} = 0 V to 3.6 V	-	-	±0.5	μΑ
OZ	OFF-state output current	$V_I = V_{IH}$ or V_{IL} (and at least one input LOW); $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.5	μΑ
OFF	power-off leakage current	V_I or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	±0.5	μΑ
Noff	additional power-off leakage current	V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.6	μА
CC	supply current	$V_1 = GND \text{ or } V_{CC}; I_O = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.9	μА
∆l _{CC}	additional supply current	$V_I = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A}; V_{CC} = 3.3 \text{ V}$	-	-	50	μΑ
Γ _{amb} =	40 °C to +125 °C					
/ _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	$0.75 \times V_{CC}$	-	-	V
		V _{CC} = 0.9 V to 1.95 V	$0.70 \times V_{CC}$	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	V
/ _{IL}	LOW-level input voltage	V _{CC} = 0.8 V	-	-	$0.25 \times V_{CC}$	V
		V _{CC} = 0.9 V to 1.95 V	-	-	$0.30 \times V_{CC}$	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V
/ _{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = 20 \mu A$; $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.11	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	$0.33 \times V_{CC}$	V
		$I_{O} = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.41	V
		$I_{O} = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.39	V
		I_{O} = 2.3 mA; V_{CC} = 2.3 V	-	-	0.36	V
		$I_{O} = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.50	V
		$I_O = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.36	V

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Table 7. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I_{l}	input leakage current	V_I = GND to 3.6 V; V_{CC} = 0 V to 3.6 V	-	-	±0.75	μΑ
l _{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL} (and at least one input LOW); $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.75	μА
I _{OFF}	power-off leakage current	V_I or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	±0.75	μΑ
ΔI_{OFF}	additional power-off leakage current	V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.75	μΑ
I _{CC}	supply current	V_I = GND or V_{CC} ; I_O = 0 A; V_{CC} = 0.8 V to 3.6 V	-	-	1.4	μΑ
ΔI_{CC}	additional supply current	$V_I = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A}; V_{CC} = 3.3 \text{ V}$	-	-	75	μΑ

11. Dynamic characteristics

Dynamic characteristics

Voltages are referenced to GND (ground = 0 V; for test circuit see Figure 9

Symbol	Parameter	Conditions			25 °C		-40 °C to +125 °C			Unit
				Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
$C_L = 5 p$	F									
t _{pd}	propagation delay	A or B to Y; see Figure 8	[2]							
		$V_{CC} = 0.8 \text{ V}$		-	13.5	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		1.9	4.6	10.4	1.8	11.4	12.6	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		1.5	3.3	6.5	1.4	7.4	8.2	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		1.2	2.9	5.1	1.1	5.9	6.5	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		1.0	2.2	3.8	0.9	4.5	4.9	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		0.9	2.3	4.0	0.8	4.5	4.9	ns
C _L = 10	pF									
t _{pd}	propagation delay	A or B to Y; see Figure 8	[2]							
		$V_{CC} = 0.8 \text{ V}$		-	16.3	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		2.3	5.6	12.3	2.1	13.7	15.1	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		1.8	4.1	7.6	1.7	8.8	9.7	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		1.6	3.8	6.1	1.4	7.1	7.8	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		1.4	2.9	4.6	1.2	5.4	5.9	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		1.3	3.2	5.7	1.1	6.4	7.0	ns
C _L = 15	pF									
t _{pd}	propagation delay	A or B to Y; see Figure 8	[2]							
		$V_{CC} = 0.8 \text{ V}$		-	19.0	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		2.6	6.6	14.2	2.4	15.8	17.4	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		2.1	4.8	8.7	1.9	10.1	11.1	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		1.9	4.6	7.6	1.7	8.5	9.3	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		1.6	3.6	5.6	1.5	6.3	6.9	ns
		V _{CC} = 3.0 V to 3.6 V		1.6	4.1	7.5	1.4	8.3	9.1	ns

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Dynamic characteristics ...continued Table 8.

Voltages are referenced to GND (ground = 0 V; for test circuit see Figure 9

Symbol	Parameter	Conditions			25 °C		-40	0 °C to +1	25 °C	Unit
				Min	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	=
C _L = 30	pF				'			'	•	
t _{pd}	propagation delay	A or B to Y; see Figure 8	[2]							
		$V_{CC} = 0.8 \text{ V}$		-	27.0	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		3.6	9.5	19.5	3.2	21.8	24.0	ns
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		2.9	7.0	11.5	2.6	13.6	15.0	ns
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		2.6	7.0	12.1	2.3	13.3	14.6	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		2.4	5.4	8.9	2.1	9.9	10.9	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		2.3	6.5	12.7	2.1	13.9	15.3	ns
$C_L = 5 p$	F, 10 pF, 15 pF and	30 pF								
C_{PD}	power dissipation capacitance	$f_i = 1 \text{ MHz};$ $V_I = \text{GND to } V_{CC}$	[3]							
		$V_{CC} = 0.8 \text{ V}$		-	0.6	-	-	-	-	pF
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$		-	0.7	-	-	-	-	pF
		$V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$		-	8.0	-	-	-	-	pF
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		-	0.9	-	-	-	-	pF
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		-	1.1	-	-	-	-	pF
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		-	1.4	-	-	-	-	рF

^[1] All typical values are measured at nominal V_{CC}.

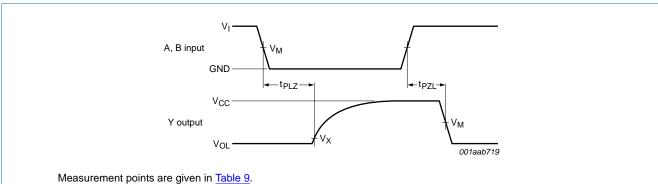
 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N$ where:

 f_i = input frequency in MHz;

V_{CC} = supply voltage in V;

N = number of inputs switching.

12. Waveforms



Logic levels: V_{OL} and V_{OH} are typical output voltage drop that occur with the output load.

The data input (A or B) to output (Y) propagation delays Fig 8.

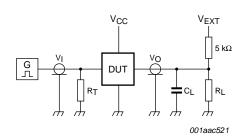
^[2] t_{pd} is the same as t_{PZL} and t_{PLZ} .

^[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

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Table 9. Measurement points

Supply voltage	Input	Output	
V _{CC}	V _M	V _M	V _X
0.8 V to 1.6 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	V _{OL} + 0.1 V
1.65 V to 2.7 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	V _{OL} + 0.15 V
3.0 V to 3.6 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	V _{OL} + 0.3 V



Test data is given in Table 10.

Definitions for test circuit:

 R_{I} = Load resistance.

 C_L = Load capacitance including jig and probe capacitance.

 R_T = Termination resistance should be equal to the output impedance Z_0 of the pulse generator.

 V_{EXT} = External voltage for measuring switching times.

Fig 9. Test circuit for measuring switching times

Table 10. Test data

Supply voltage	Load		V _{EXT}					
V _{CC}	CL	R _L [1]	t _{PLH} , t _{PHL}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}			
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 k Ω or 1 M Ω	open	GND	$2 \times V_{CC}$			

^[1] For measuring enable and disable times $R_L = 5 \text{ k}\Omega$, for measuring propagation delays, setup and hold times and pulse width $R_L = 1 \text{ M}\Omega$.

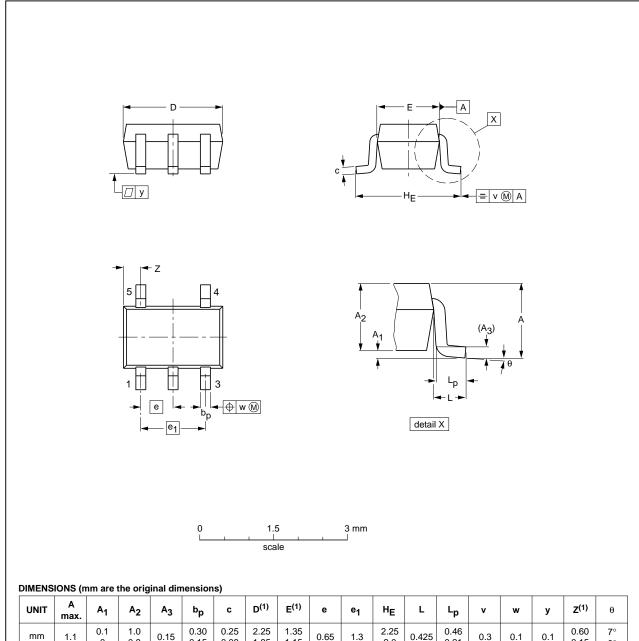
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13. Package outline

TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mm

SOT353-1



UNIT	A max.	A ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E ⁽¹⁾	е	e ₁	HE	L	Lp	v	w	у	Z ⁽¹⁾	θ
mm	1.1	0.1 0	1.0 0.8	0.15	0.30 0.15	0.25 0.08	2.25 1.85	1.35 1.15	0.65	1.3	2.25 2.0	0.425	0.46 0.21	0.3	0.1	0.1	0.60 0.15	7° 0°

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

	REFER	EUROPEAN	ISSUE DATE		
IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
	MO-203	SC-88A			-00-09-01 03-02-19
	IEC	IEC JEDEC		IEC JEDEC JEITA	IEC JEDEC JEITA PROJECTION

Fig 10. Package outline SOT353-1 (TSSOP5)

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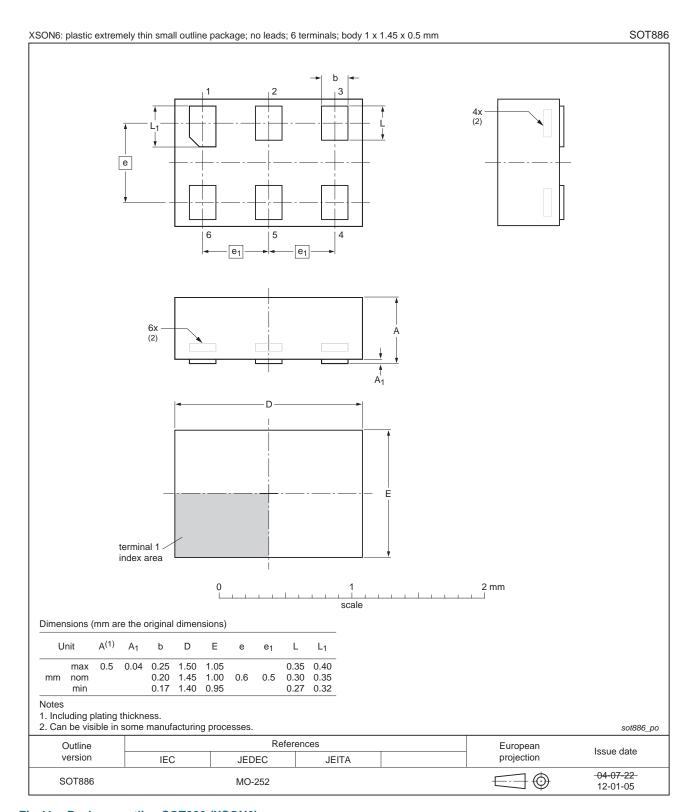


Fig 11. Package outline SOT886 (XSON6)

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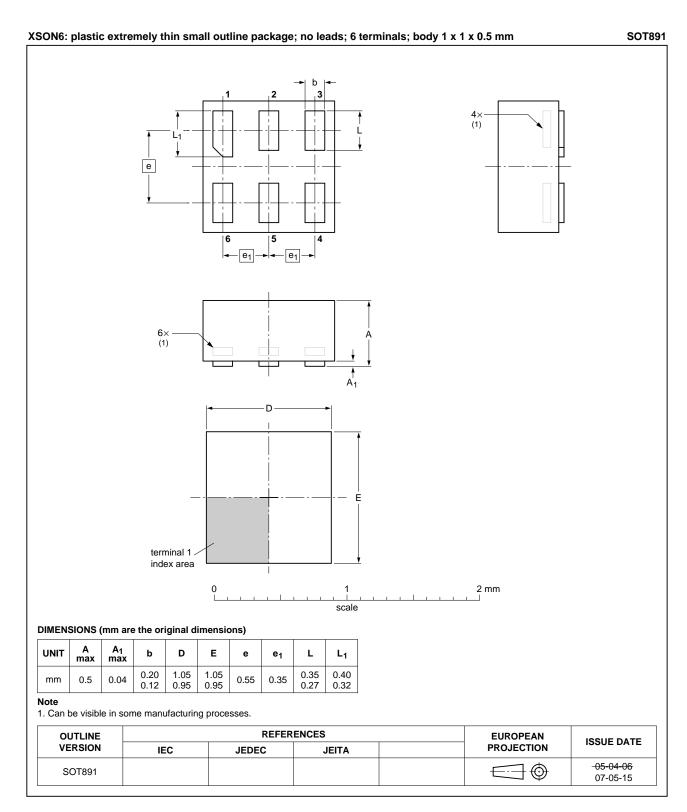


Fig 12. Package outline SOT891 (XSON6)

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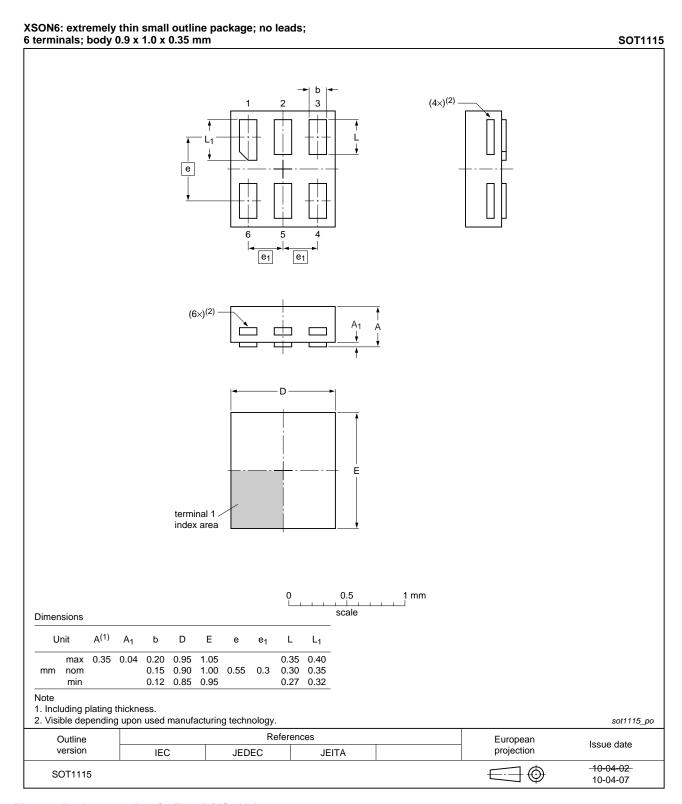


Fig 13. Package outline SOT1115 (XSON6)

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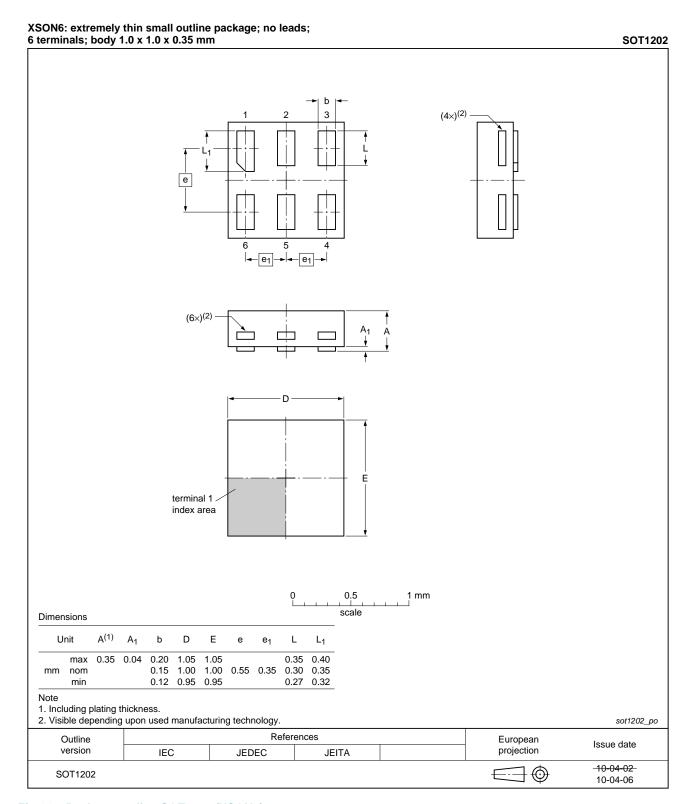


Fig 14. Package outline SOT1202 (XSON6)

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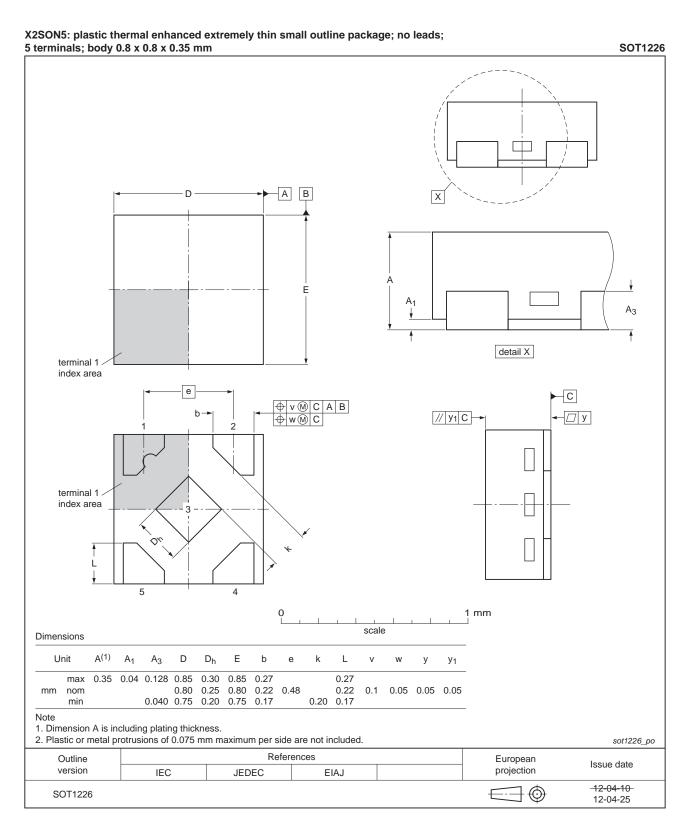


Fig 15. Package outline SOT1226 (X2SON5)

Product data sheet

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14. Abbreviations

Table 11. Abbreviations

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MM	Machine Model

15. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AUP1G38 v.6	20120628	Product data sheet	-	74AUP1G38 v.5
Modifications:	 Added type n 	umber 74AUP1G38GX (SO	T1226)	
	 Package outl 	ine drawing of SOT886 (<u>Fig</u> u	ure 11) modified.	
74AUP1G38 v.5	20111129	Product data sheet	-	74AUP1G38 v.4
Modifications:	 Legal pages 	updated.		
74AUP1G38 v.4	20101007	Product data sheet	-	74AUP1G38 v.3
74AUP1G38 v.3	20090622	Product data sheet	-	74AUP1G38 v.2
74AUP1G38 v.2	20070614	Product data sheet	-	74AUP1G38 v.1
74AUP1G38 v.1	20061020	Product data sheet	-	-

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16. Legal information

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Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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